CHEMICAL VAPOR DEPOSITION (CVD)
OR PLASMA ENHANCED CVD OF
SILICON OR TUNGSTEN CONTAINING
FILMS IN A CVD CHAMBER.

FLUORINE BASED CLEANING PLASMA
(IN SITU OR REMOTE) TO REMOVE
DEPOSITS FROM THE INTERIOR SURFACES
OF THE CVD CHAMBER.

IN SITU CLEANING PLASMA OF A
HYDROGEN CONTAINING GAS AND AN
OXYGEN CONTAINING GAS TO REMOVE
FLUORINE RESIDES FROM THE INTERIOR
SURFACES OF THE CVD CHAMBER.

Figure 1

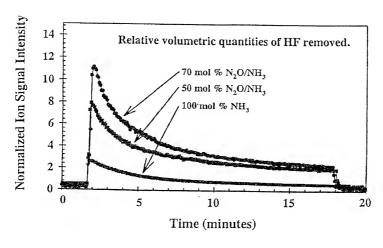


Figure 2

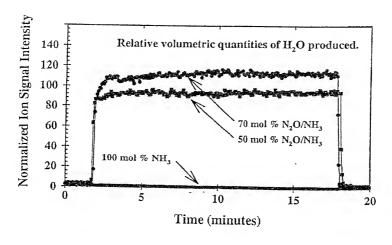


Figure 3

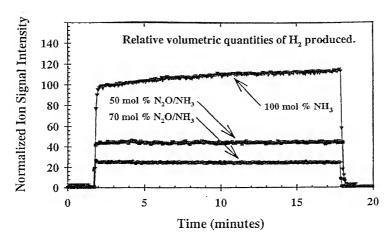


Figure 4

